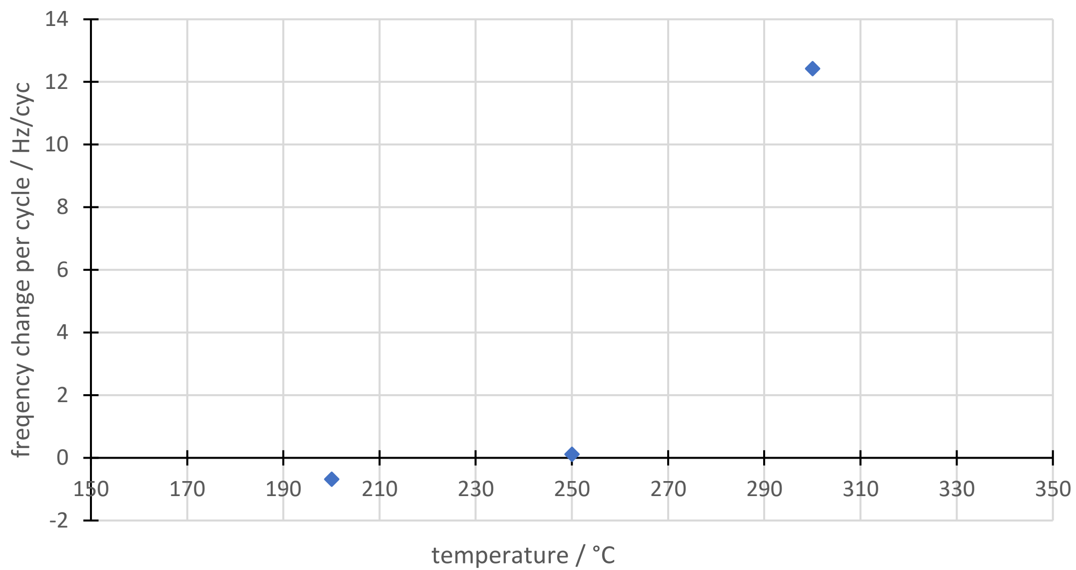
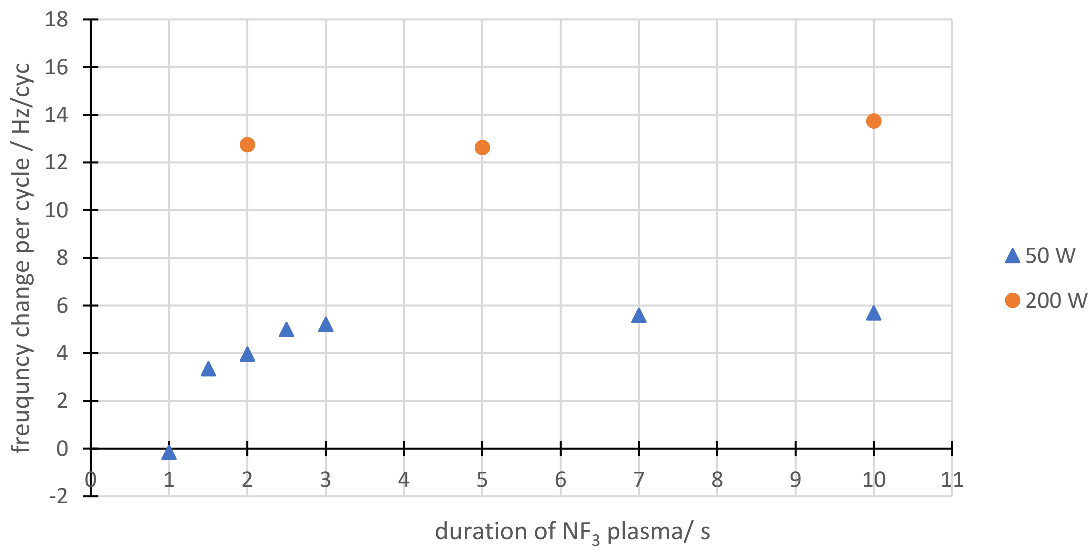
Temperature variation



Dependence of the frequency change per cycle on the process temperature at 10 s precursor pulse time, with layer deposition at 200 °C, limited range between deposition and etching at 250 °C and pulse time-dependent etching at 300 °C

NF_3 plasma time variation



Influence of NF_3 plasma time variation on frequency change per cycle